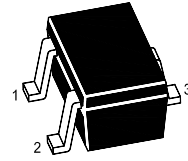
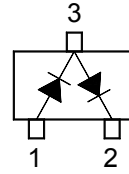


BAV99W-AH

Silicon Epitaxial Planar Switching Diode

Features

- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant



SOT-323 Plastic Package

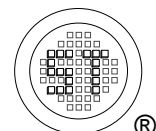
Marking Code: **A7**

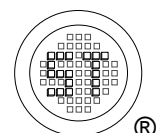
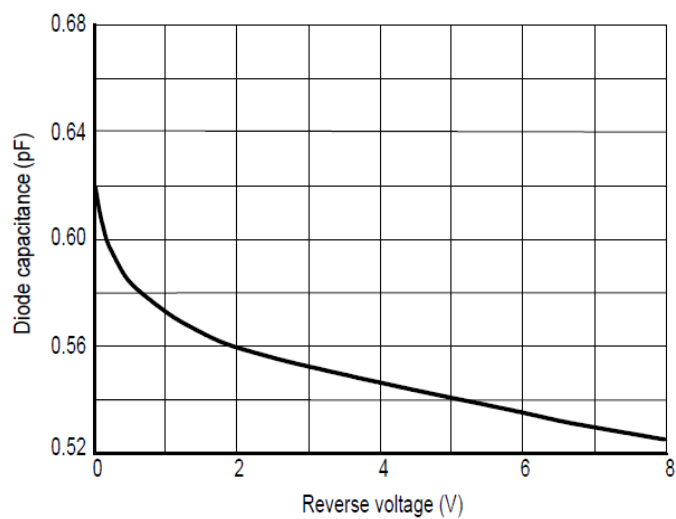
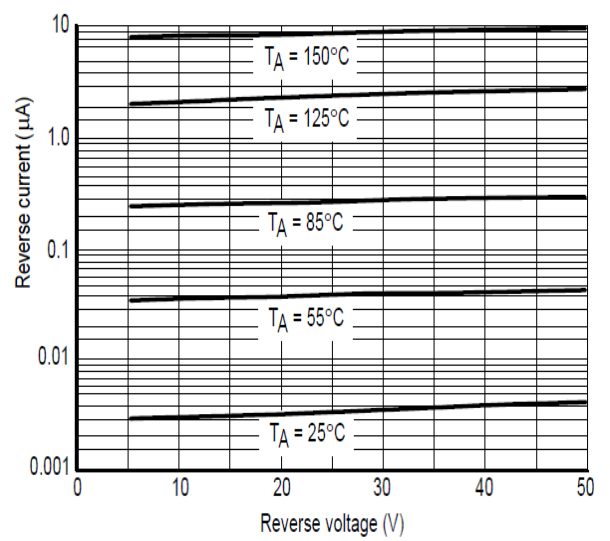
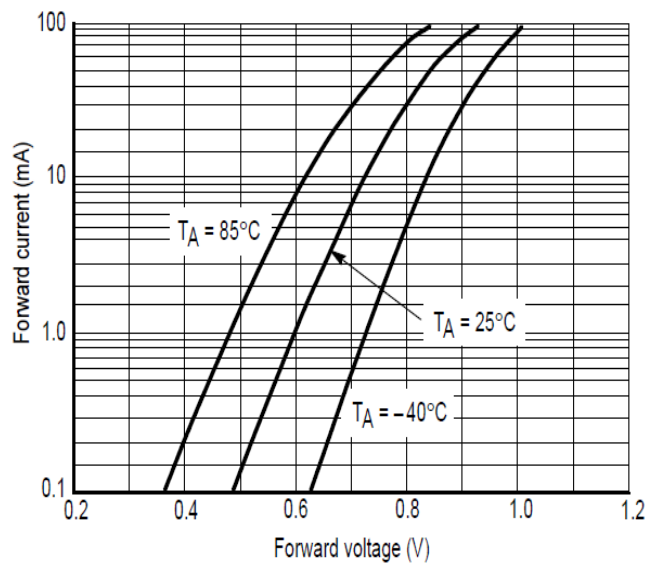
Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	100	V
Continuous Forward Current	I_F	150	mA
Single Diode Load		130	
Double Diode Load			
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	4	A
at $t = 1\text{ }\mu\text{s}$		1	
at $t = 1\text{ ms}$		0.5	
at $t = 1\text{ s}$			
Total Power Dissipation	P_{tot}	200	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}\text{C/W}$
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

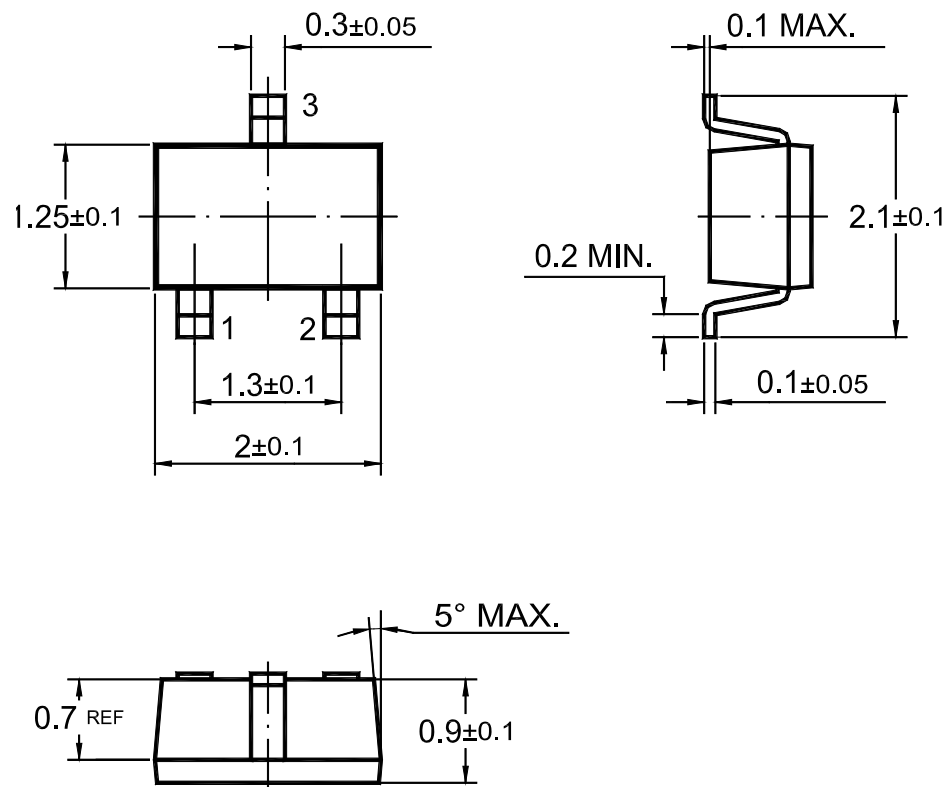
Parameter	Symbol	Max.	Unit
Forward Voltage	V_F		V
at $I_F = 1\text{ mA}$		0.715	
at $I_F = 10\text{ mA}$		0.855	
at $I_F = 50\text{ mA}$		1	
at $I_F = 150\text{ mA}$		1.25	
Reverse Current	I_R		nA μA μA μA
at $V_R = 25\text{ V}$		30	
at $V_R = 80\text{ V}$		0.5	
at $V_R = 25\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$		30	
at $V_R = 80\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$		50	
Diode Capacitance	C_d		pF
at $V_R = 0, f = 1\text{ MHz}$		1.5	
Reverse Recovery Time	t_{rr}		ns
at $I_F = 10\text{ mA}, I_R = 60\text{ mA}, I_{rr} = 0.1 \times I_R$		4	



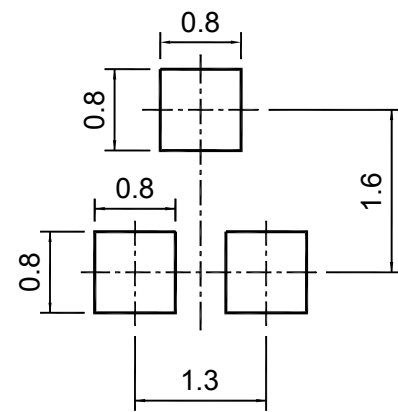


PACKAGE OUTLINE(Dimensions in mm)

SOT-323



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-323	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

